

PHASE CONTROL THYRISTORS

Hockey Puk Version

Features

- Center amplifying gate
- Metal case with ceramic insulator
- International standard case TO-200AB (E-PUK)
- Low profile hockey-puk to increase current-carrying capability
- Extended temperature range
- Lead Free

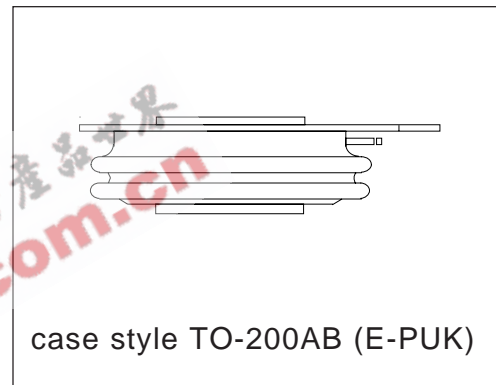
960A

Typical Applications

- DC motor controls
- Controlled DC power supplies
- AC controllers

Major Ratings and Characteristics

Parameters	ST380CH..C	Units	
$I_{T(AV)}$	960	A	
@ T_{hs}	80	°C	
$I_{T(RMS)}$	2220	A	
@ T_{hs}	25	°C	
I_{TSM}	@ 50Hz	12500	A
	@ 60Hz	13000	A
I^2t	@ 50Hz	782	KA ² s
	@ 60Hz	713	KA ² s
V_{DRM}/V_{RRM}	400 to 600	V	
t_q	typical	100	μs
T_J	- 40 to 150	°C	



ELECTRICAL SPECIFICATIONS

Voltage Ratings

Type number	Voltage Code	V_{DRM}/V_{RRM} , max. repetitive peak and off-state voltage V	V_{RSM} , maximum non-repetitive peak voltage V	I_{DRM}/I_{RRM} max. @ $T_J = T_J$ max mA
ST380CH..C	04	400	500	100
	06	600	700	

On-state Conduction

Parameter	ST380CH..C	Units	Conditions
$I_{T(AV)}$ Max. average on-state current @ Heatsink temperature	960 (440)	A	180° conduction, half sine wave double side (single side) cooled
	80 (110)	°C	
$I_{T(RMS)}$ Max. RMS on-state current	2220		DC @ 25°C heatsink temperature double side cooled
I_{TSM} Max. peak, one-cycle non-repetitive surge current	12500	A	t = 10ms No voltage
	13000		t = 8.3ms reapplied
	10500		t = 10ms 100% V_{RRM}
I^2t Maximum I^2t for fusing	11000	KA ² s	t = 8.3ms reapplied
	782		t = 10ms No voltage
	713		t = 8.3ms reapplied
	553		t = 10ms 100% V_{RRM}
	505		t = 8.3ms reapplied
$I^2\sqrt{t}$ Maximum $I^2\sqrt{t}$ for fusing	7820	KA ² √s	t = 0.1 to 10ms, no voltage reapplied
$V_{T(TO)1}$ Low level value of threshold voltage	0.85	V	(16.7% $\times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)}$), $T_J = T_J$ max.
	0.88		($I > \pi \times I_{T(AV)}$), $T_J = T_J$ max.
r_{t1} Low level value of on-state slope resistance	0.25	mΩ	(16.7% $\times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)}$), $T_J = T_J$ max.
	0.24		($I > \pi \times I_{T(AV)}$), $T_J = T_J$ max.
V_{TM} Max. on-state voltage	1.58	V	$I_{pk} = 2900A$, $T_J = T_J$ max, $t_p = 10ms$ sine pulse $T_J = 25^\circ C$, anode supply 12V resistive load
I_H Maximum holding current	600	mA	
I_L Typical latching current	1000		

Switching

Parameter	ST380CH..C	Units	Conditions
di/dt Max. non-repetitive rate of rise of turned-on current	1000	A/μs	Gate drive 20V, 20Ω, $t_r \leq 1\mu s$ $T_J = T_J$ max, anode voltage $\leq 80\% V_{DRM}$
t_d Typical delay time	1.0	μs	Gate current 1A, $di_g/dt = 1A/\mu s$ $V_d = 0.67\% V_{DRM}$, $T_J = 25^\circ C$
t_q Typical turn-off time	100		$I_{TM} = 550A$, $T_J = T_J$ max, $di/dt = 40A/\mu s$, $V_R = 50V$ $dv/dt = 20V/\mu s$, Gate 0V 100Ω, $t_p = 500\mu s$

Blocking

Parameter	ST380CH..C	Units	Conditions
dv/dt Maximum critical rate of rise of	500 off-state voltage	V/μs	T _J = T _J max. linear to 80% rated V _{DRM}
I _{RRM} I _{DRM} Max. peak reverse and off-state leakage current	100	mA	T _J = T _J max, rated V _{DRM} /V _{RRM} applied

Triggering

Parameter	ST380CH..C		Units	Conditions	
P _{GM} Maximum peak gate power	10.0		W	T _J = T _J max, t _p ≤ 5ms	
P _{G(AV)} Maximum average gate power	2.0			T _J = T _J max, f = 50Hz, d% = 50	
I _{GM} Max. peak positive gate current	3.0		A	T _J = T _J max, t _p ≤ 5ms	
+V _{GM} Maximum peak positive gate voltage	20		V	T _J = T _J max, t _p ≤ 5ms	
-V _{GM} Maximum peak negative gate voltage	5.0				
I _{GT} DC gate current required to trigger	TYP.	MAX.	mA	Max. required gate trigger/ current/ voltage are the lowest value which will trigger all units 12V anode-to-cathode applied	
	200	-			T _J = -40°C
	100	200			T _J = 25°C
V _{GT} DC gate voltage required to trigger	40	-	V	T _J = 150°C	
	2.5	-		T _J = -40°C	
	1.8	3.0		T _J = 25°C	
I _{GD} DC gate current not to trigger	10		mA	Max. gate current/voltage not to trigger is the max. value which will not trigger any unit with rated V _{DRM} anode-to-cathode applied	
	0.25				T _J = T _J max
V _{GD} DC gate voltage not to trigger	0.25		V		

Thermal and Mechanical Specification

Parameter	ST380CH..C	Units	Conditions
T _J Max. operating temperature range	-40 to 150	°C	
T _{stg} Max. storage temperature range	-40 to 150		
R _{thJ-hs} Max. thermal resistance, junction to heatsink	0.09 0.04	K/W	DC operation single side cooled DC operation double side cooled
R _{thC-hs} Max. thermal resistance, case to heatsink	0.02 0.01	K/W	DC operation single side cooled DC operation double side cooled
F Mounting force, ± 10%	9800 (1000)	N (Kg)	
wt Approximate weight	83	g	
Case style	TO-200AB (E-PUK)		See Outline Table

ΔR_{thJ-hs} Conduction

(The following table shows the increment of thermal resistance R_{thJ-hs} when devices operate at different conduction angles than DC)

Conduction angle	Sinusoidal conduction		Rectangular conduction		Units	Conditions
	Single Side	Double Side	Single Side	Double Side		
180°	0.010	0.011	0.007	0.007	K/W	$T_J = T_{J \text{ max.}}$
120°	0.012	0.012	0.012	0.013		
90°	0.015	0.015	0.016	0.017		
60°	0.022	0.022	0.023	0.023		
30°	0.036	0.036	0.036	0.037		

Ordering Information Table

Device Code

ST	38	0	CH	06	C	1	PbF
1	2	3	4	5	6	7	8

- 1** - Thyristor
- 2** - Essential part number
- 3** - 0= Converter grade
- 4** - CH = Ceramic Puk, High temperature
- 5** - Voltage code: Code x 100 = V_{RRM} (See Voltage Rating Table)
- 6** - C = Puk Case TO-200AB (E-PUK)
- 7** - 0 = Eyelet terminals (Gate and Auxiliary Cathode Unsoldered Leads)
 1 = Fast-on terminals (Gate and Auxiliary Cathode Unsoldered Leads)
 2 = Eyelet terminals (Gate and Auxiliary Cathode Soldered Leads)
 3 = Fast-on terminals (Gate and Auxiliary Cathode Soldered Leads)
- 8** - Critical dv/dt: None = 500V/ μ sec (Standard selection)
 L = 1000V/ μ sec (Special selection)
- 9** - Lead Free

Outline Table

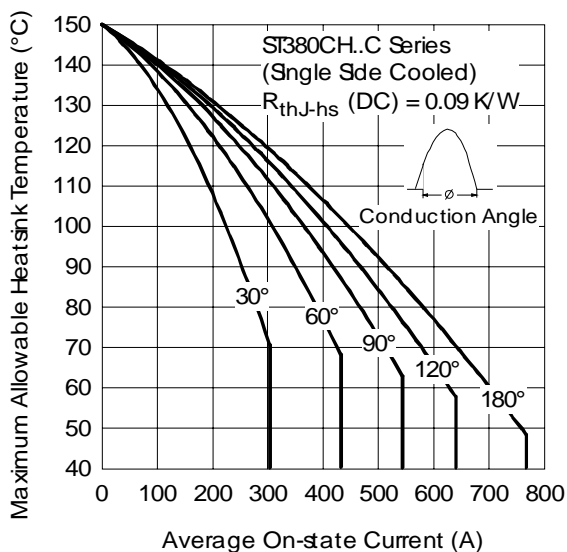
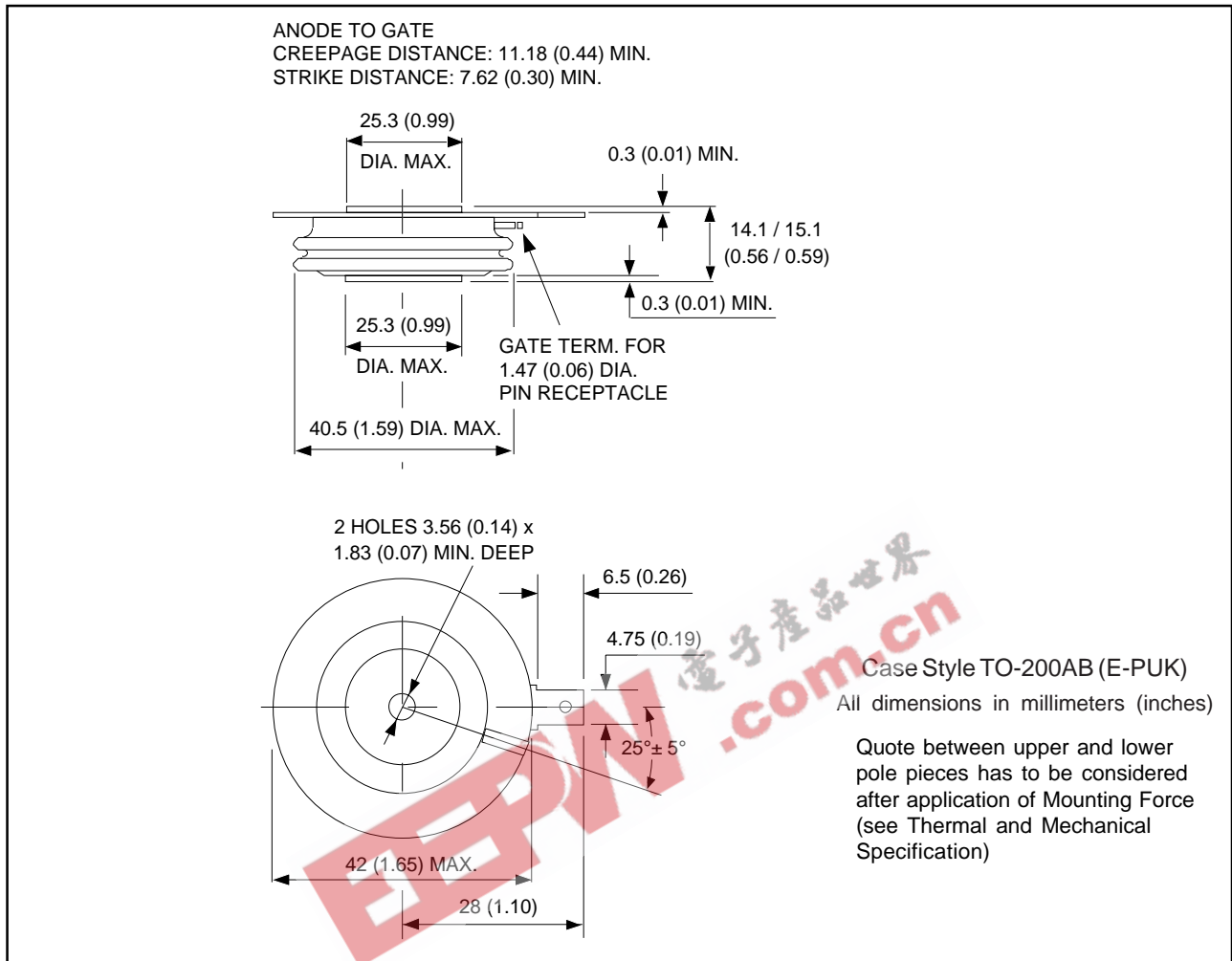


Fig. 1 - Current Ratings Characteristics

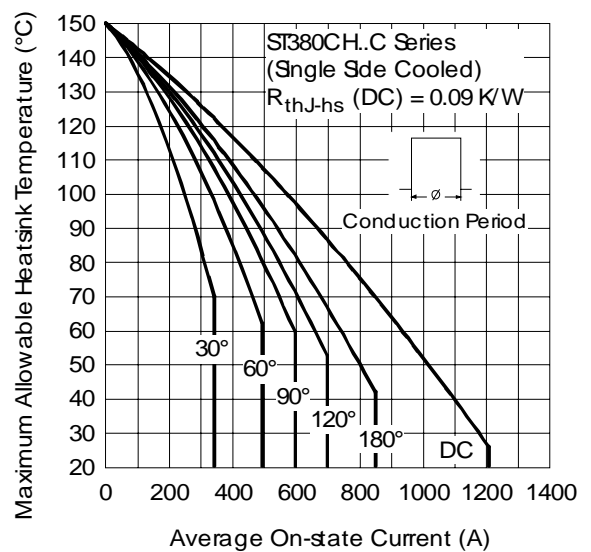


Fig. 2 - Current Ratings Characteristics

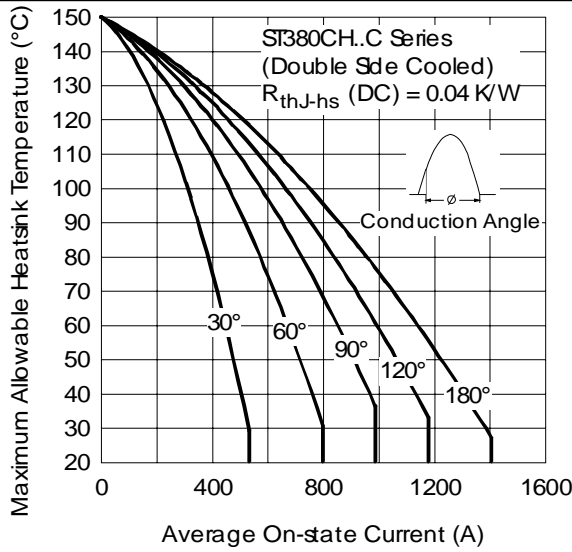


Fig. 3 - Current Ratings Characteristics

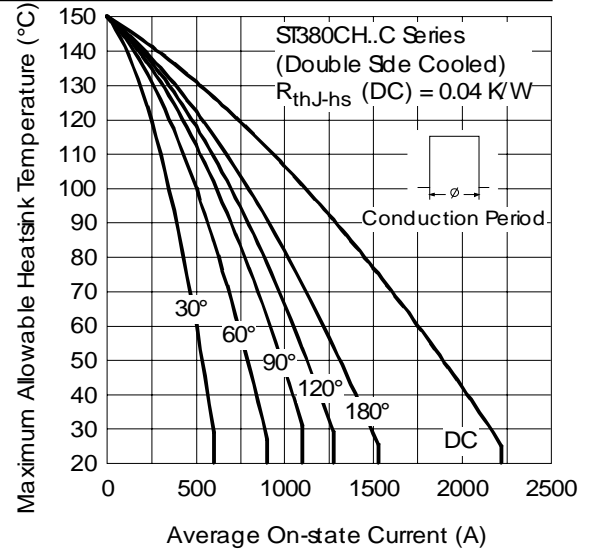


Fig. 4 - Current Ratings Characteristics

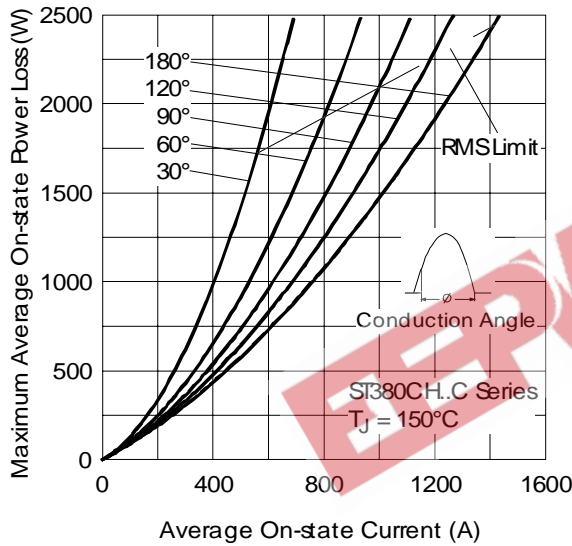


Fig. 5- On-state Power Loss Characteristics

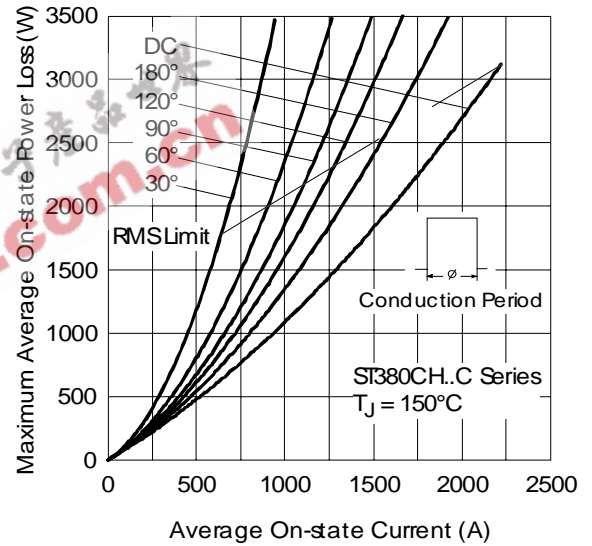


Fig. 6- On-state Power Loss Characteristics

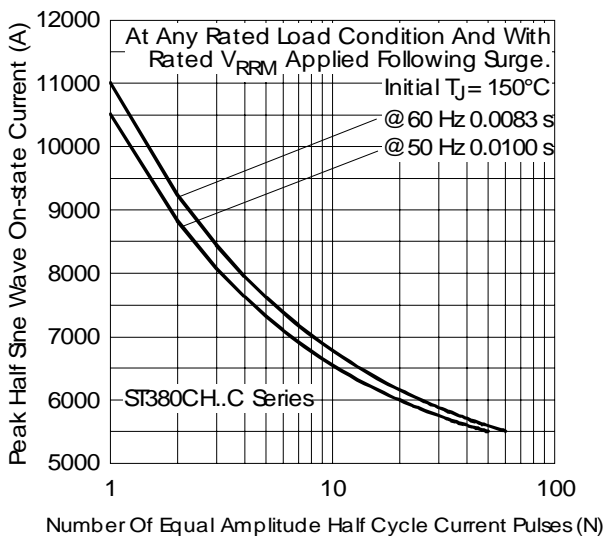


Fig. 7 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

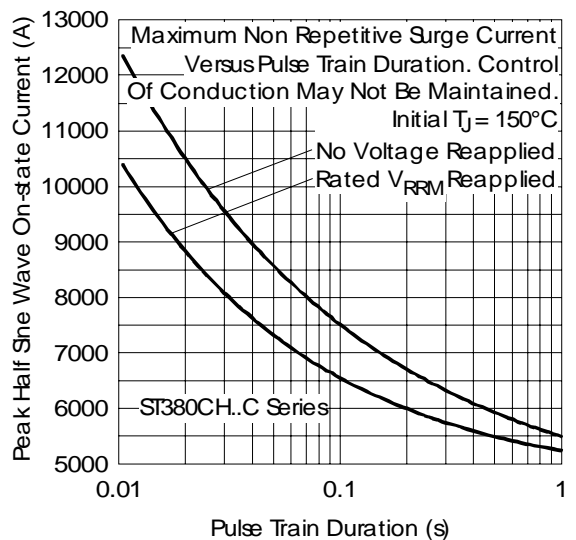


Fig. 8 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

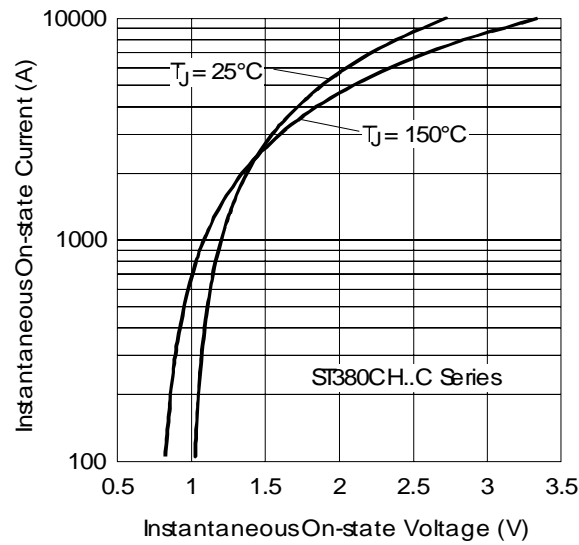


Fig. 9 - On-state Voltage Drop Characteristics

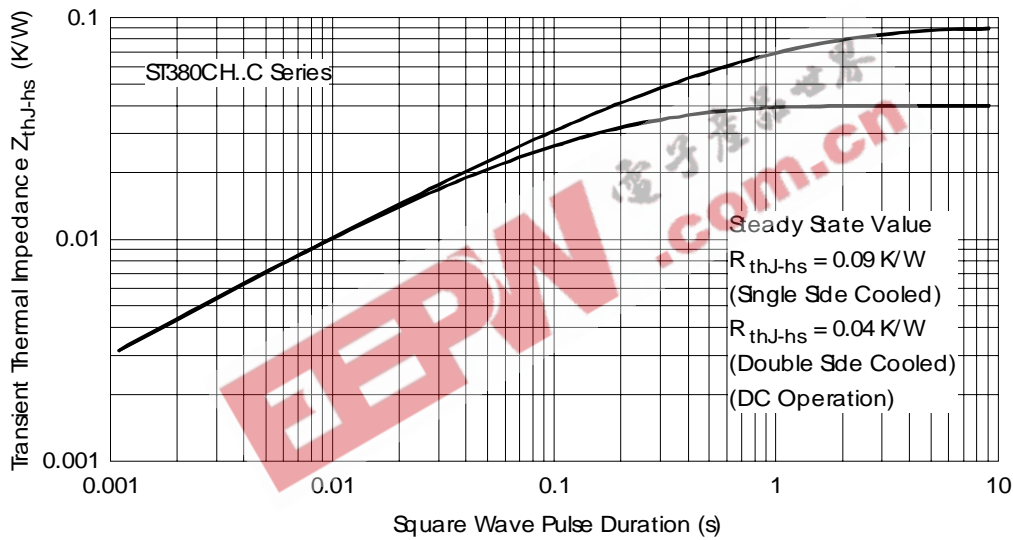


Fig. 10 - Thermal Impedance Z_{thJ-hs} Characteristics

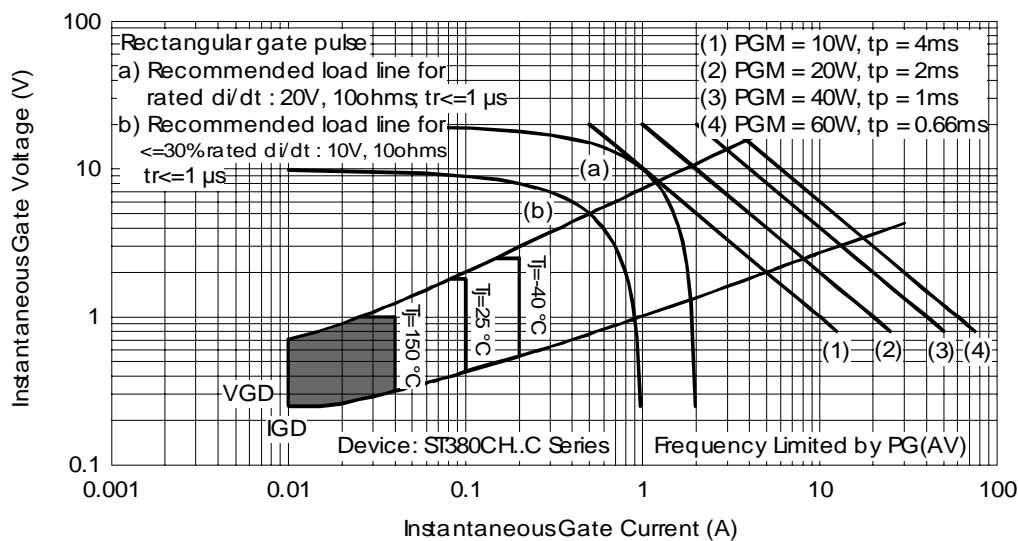


Fig. 11 - Gate Characteristics

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Data and specifications subject to change without notice.
This product has been designed and qualified for Industrial Level.
Qualification Standards can be found on IR's Web site.

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IR WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105
TAC Fax: (310) 252-7309

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